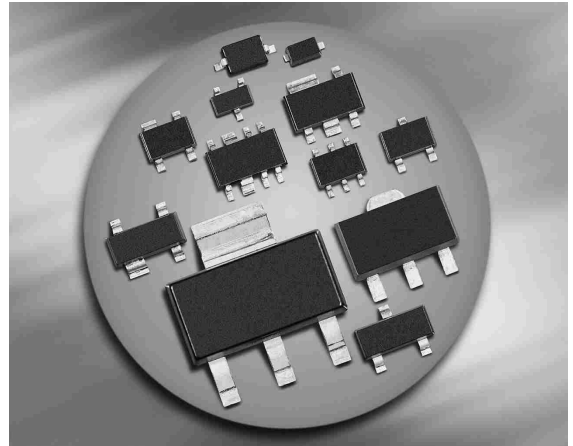


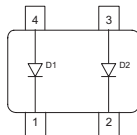
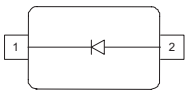
Silicon PIN Diode

- Series diode for mobile communication in low loss transmit-receiver switches
- Band switch for TV-tuners
- Very low forward resistance (typ. 0.65Ω @ 5 mA)
- Low capacitance (typ. 0.5 pF @ 0V)
- Fast switching applications



BAR65-02L
BAR65-02V
BAR65-03W

BAR65-07



Type	Package	Configuration	$L_S(\text{nH})$	Marking
BAR65-02L *	TSLP-2-1	single, leadless	0.4	NN
BAR65-02V	SC79	single	0.6	N
BAR65-03W	SOD323	single	1.8	M/blue
BAR65-07	SOT143	parallel pair	2	Ms

* Preliminary Data

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Total power dissipation	P_{tot}		mW
BAR65-02L, $T_S \leq 128^\circ\text{C}$		250	
BAR65-02V, $T_S \leq 118^\circ\text{C}$		250	
BAR65-03W, $T_S \leq 113^\circ\text{C}$		250	
BAR65-07, $T_S \leq 57^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BAR65-02L		≤ 90	
BAR65-02V		≤ 130	
BAR65-03W		≤ 145	
BAR65-07		≤ 370	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 20\text{ V}$	I_R	-	-	20	nA
Forward voltage $I_F = 100\text{ mA}$	V_F	-	0.93	1	V

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

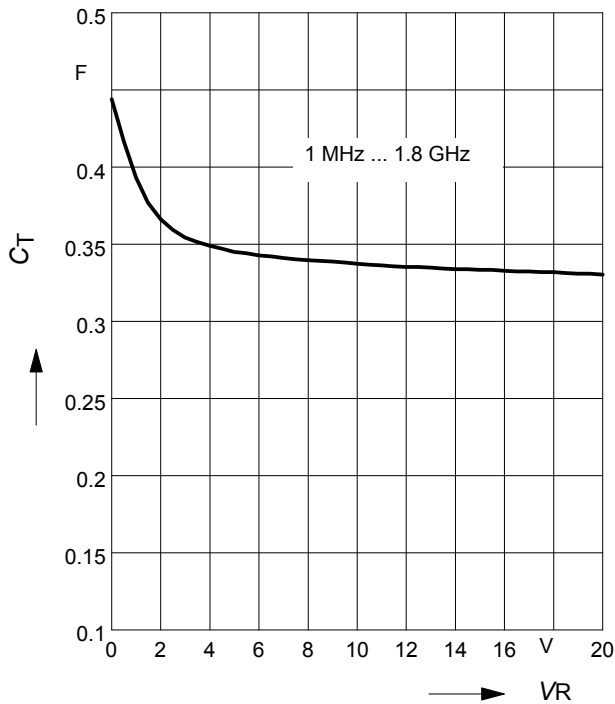
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}$, $f = 1\text{ MHz}$ $V_R = 3\text{ V}$, $f = 1\text{ MHz}$ $V_R = 0\text{ V}$, $f = 100\text{ MHz} \dots 1.8\text{ GHz}$	C_T	- - -	0.45 0.4 0.5	0.9 0.8 -	pF
Reverse parallel resistance $V_R = 0\text{ V}$, $f = 100\text{ MHz}$ $V_R = 0\text{ V}$, $f = 1\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$	R_P	- - -	700 10 5	- - -	kΩ
Forward resistance $I_F = 1\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 5\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$	r_f	- - -	1 0.65 0.56	- 0.95 0.9	Ω
Charge carrier life time $I_F = 10\text{ mA}$, $I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$	τ_{rr}	-	80	-	ns
I-region width	W_I	-	3.5	-	μm
Insertion loss ¹⁾ $I_F = 1\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 5\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 10\text{ mA}$, $f = 1.8\text{ GHz}$	$ S_{21} ^2$	- - -	-0.08 -0.06 -0.05	- - -	dB
Isolation ¹⁾ $V_R = 0\text{ V}$, $f = 0.9\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$ $V_R = 0\text{ V}$, $f = 2.45\text{ GHz}$	$ S_{21} ^2$	- - -	-12 -7 -5	- - -	

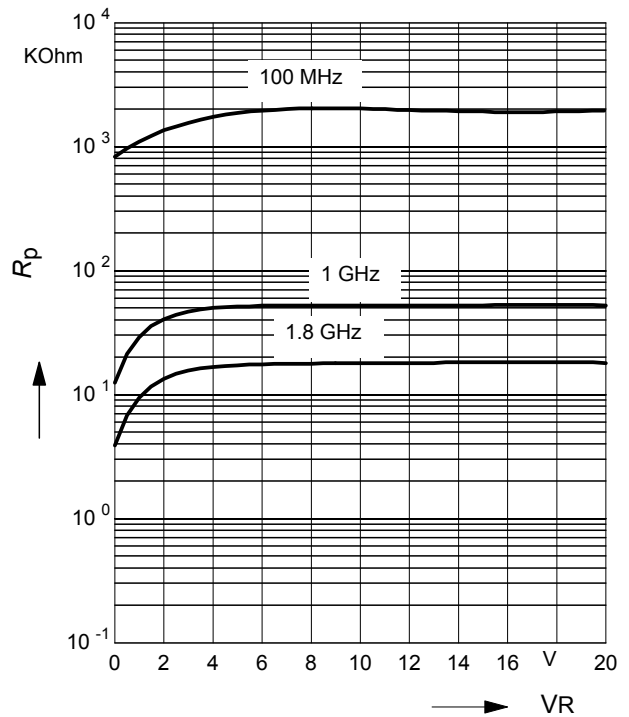
¹⁾BAR65-02L in series configuration, $Z = 50\ \Omega$

Diode capacitance $C_T = f(V_R)$

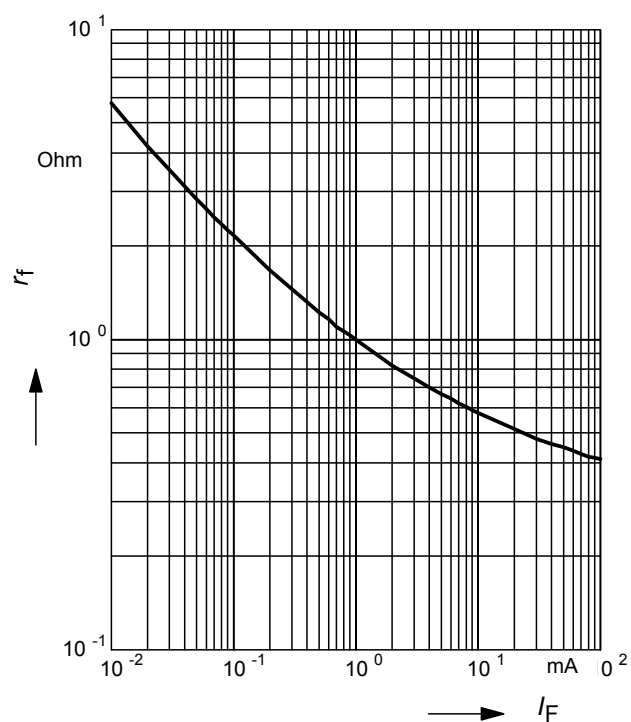
f = Parameter


Reverse parallel resistance $R_P = f(V_R)$

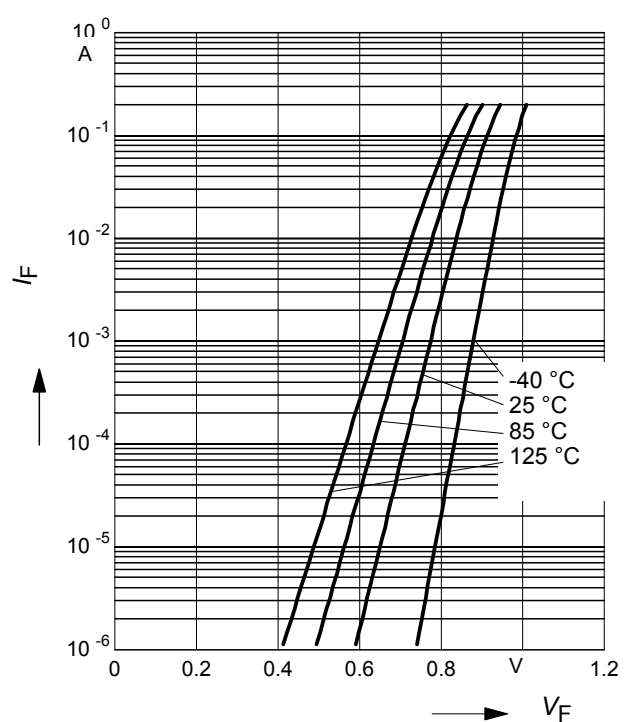
f = Parameter

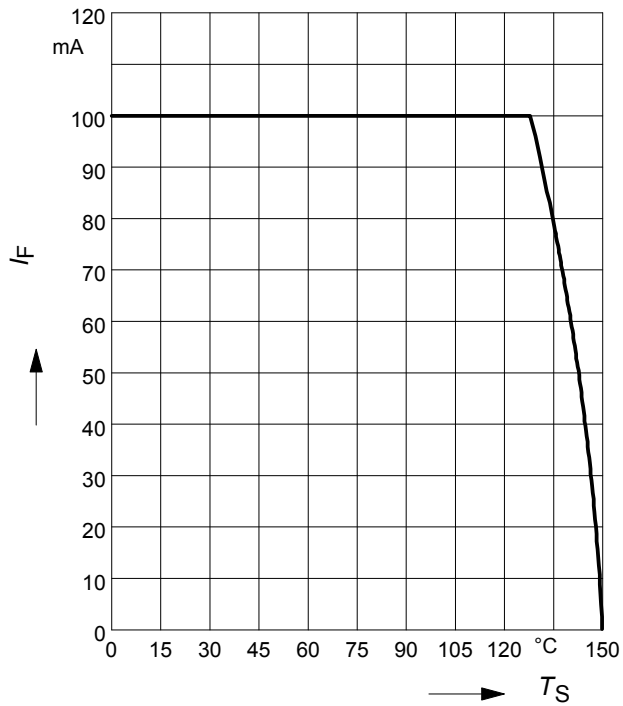
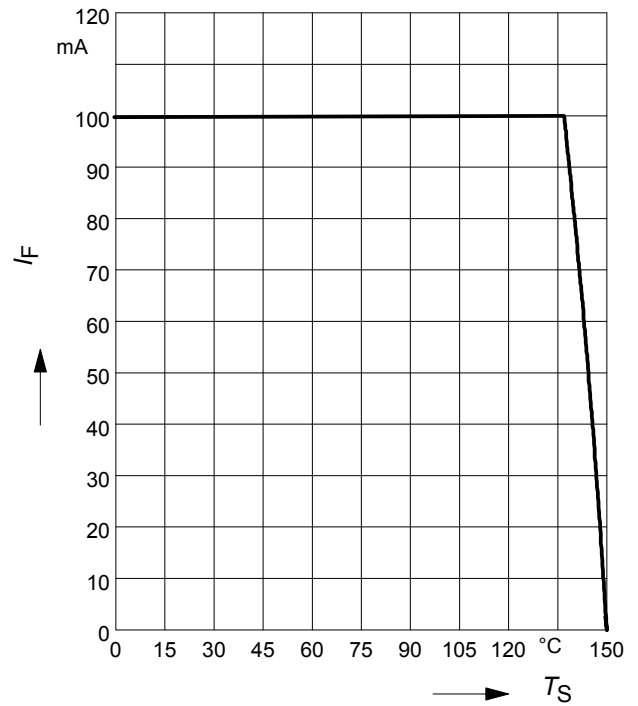
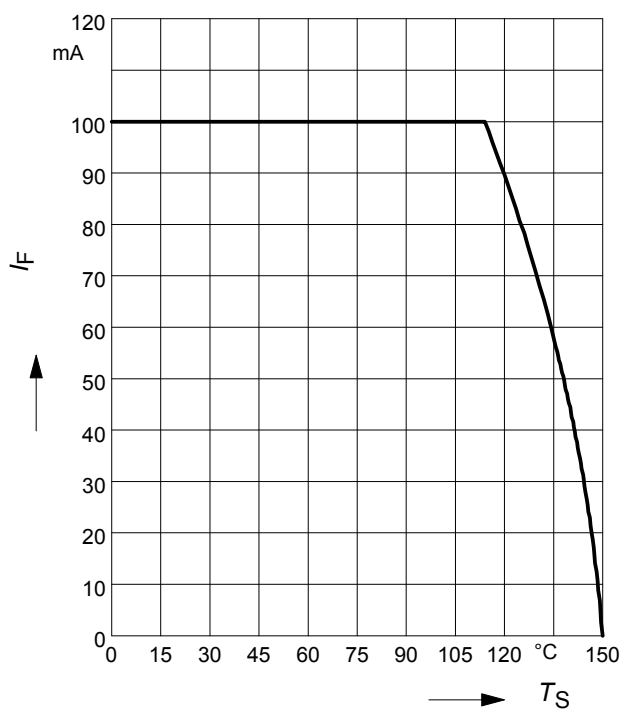
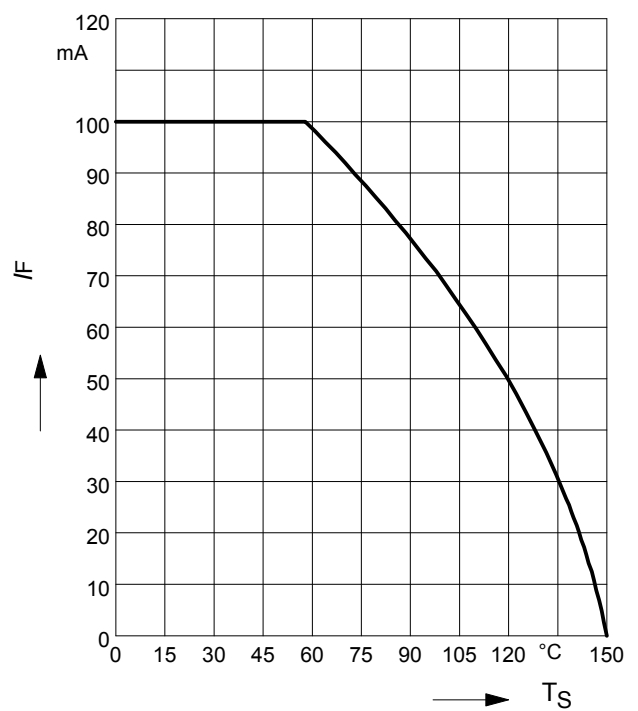

Forward resistance $r_f = f(I_F)$

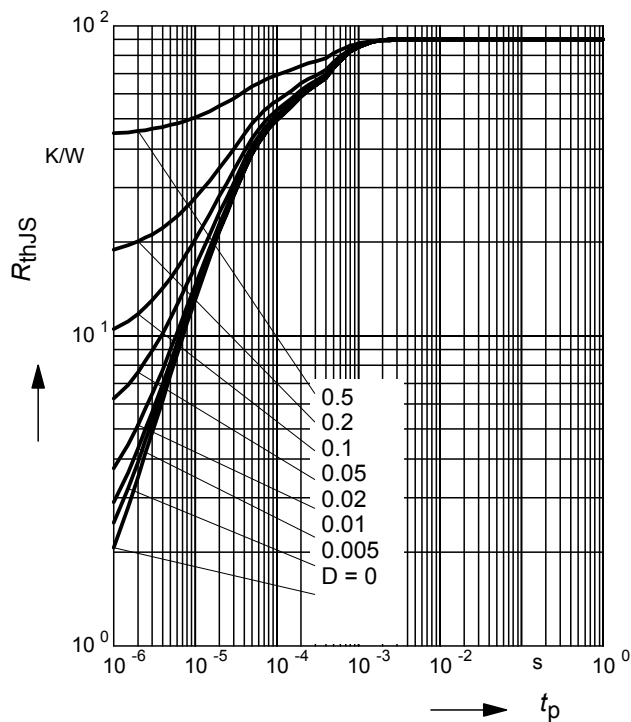
f = 100MHz


Forward current $I_F = f(V_F)$

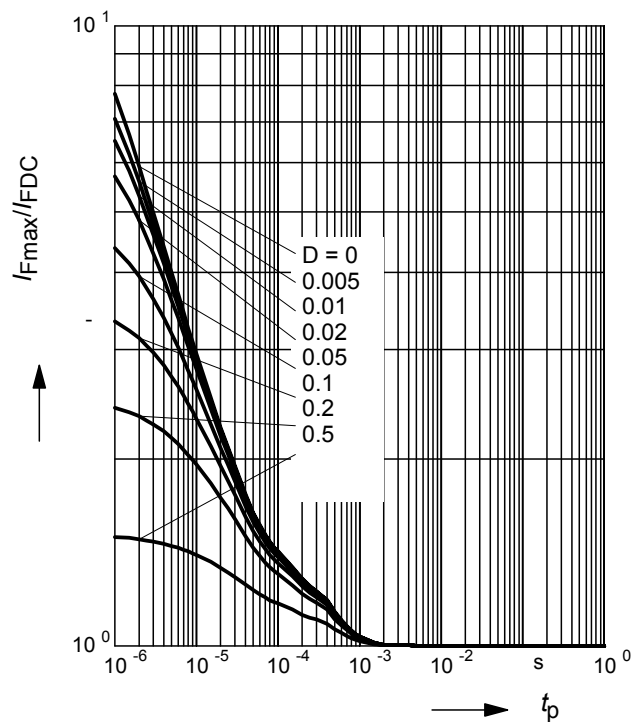
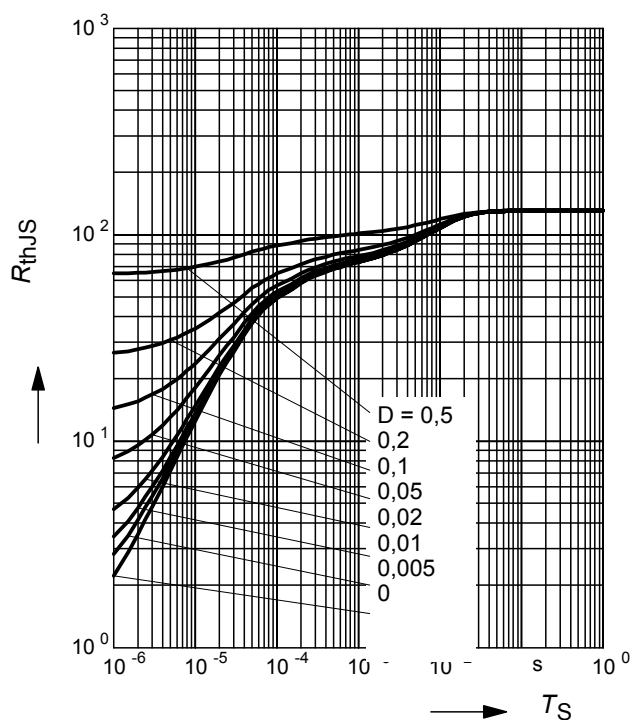
T_A = Parameter



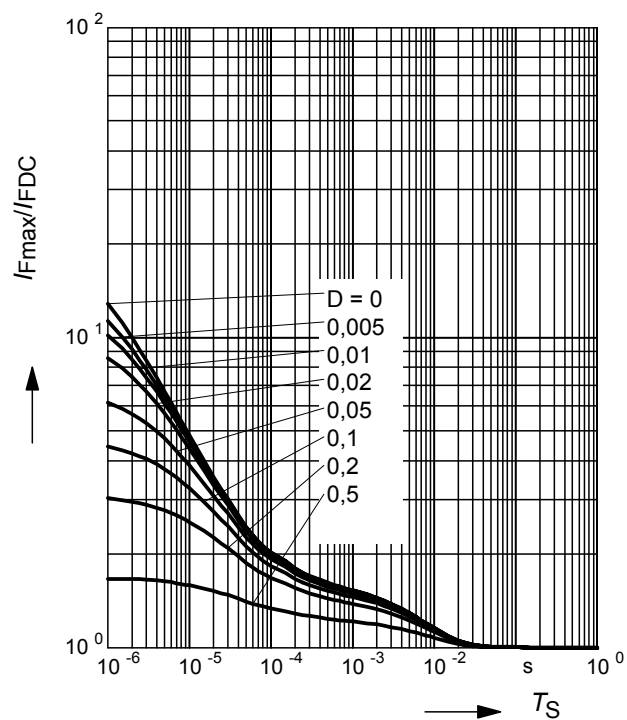
Forward current $I_F = f(T_S)$
BAR65-02L

Forward current $I_F = f(T_S)$
BAR65-02V

Forward current $I_F = f(T_S)$
BAR65-03W

Forward current $I_F = f(T_S)$
BAR65-07


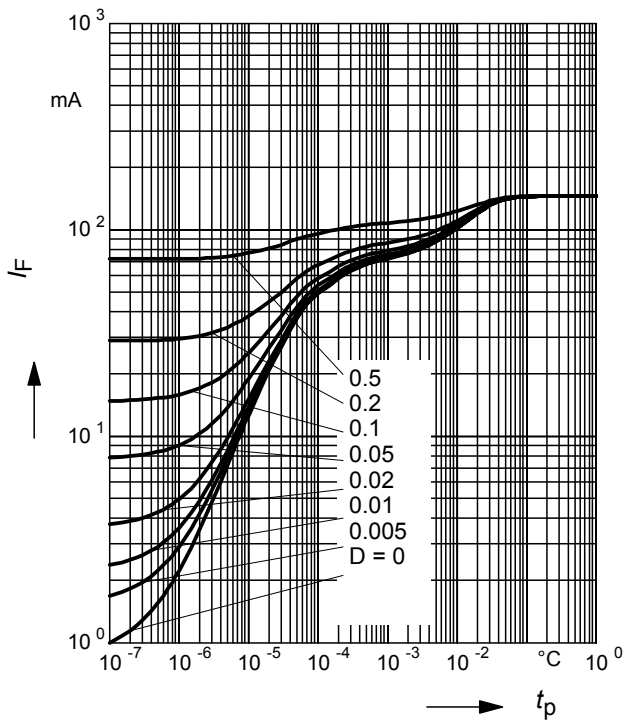
Permissible Puls Load $R_{thJS} = f(t_p)$
BAR65-02L

Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

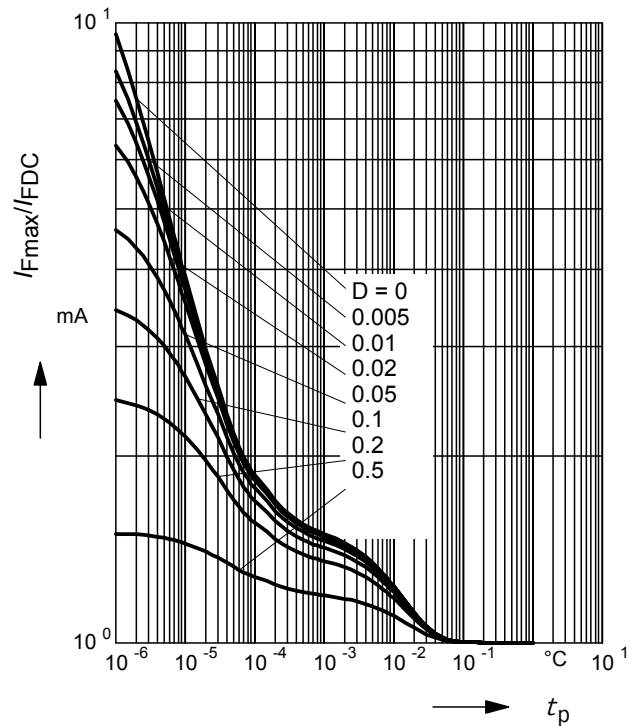
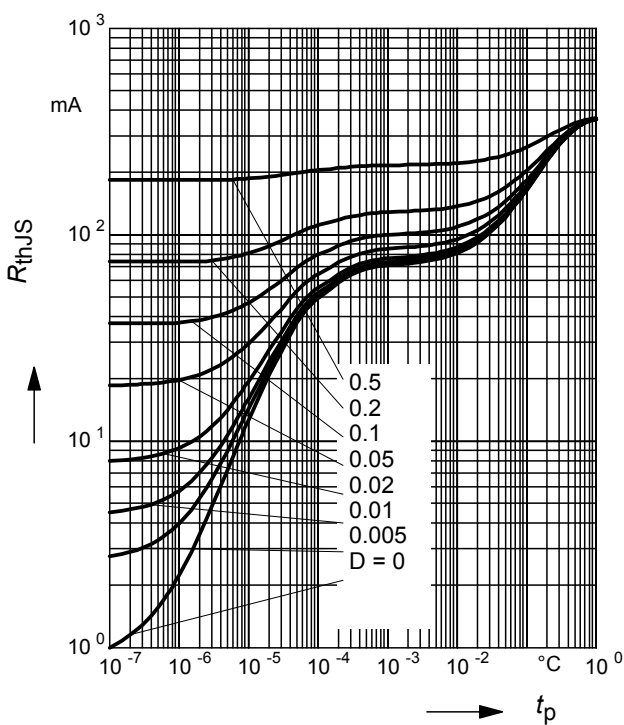
BAR65-02L

Permissible Puls Load $R_{thJS} = f(t_p)$
BAR65-02V

Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

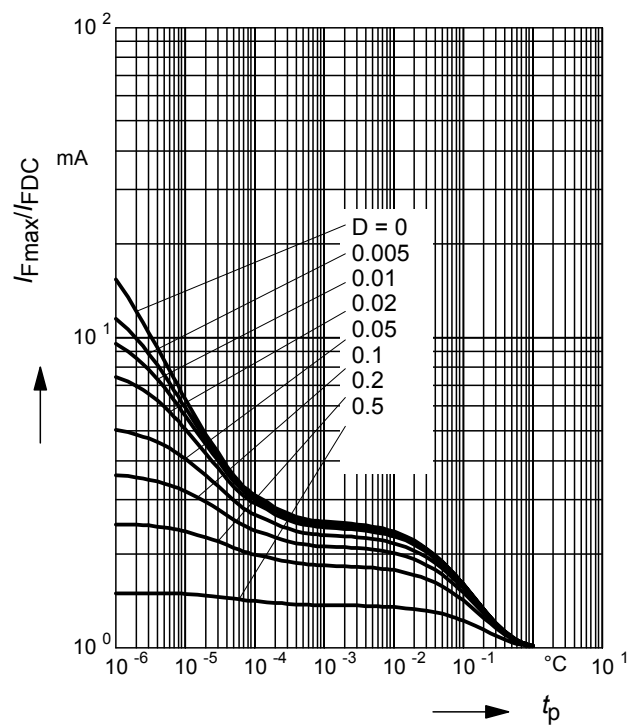
BAR65-02V


Permissible Puls Load $R_{thJS} = f(t_p)$
BAR65-03W

Permissible Pulse Load

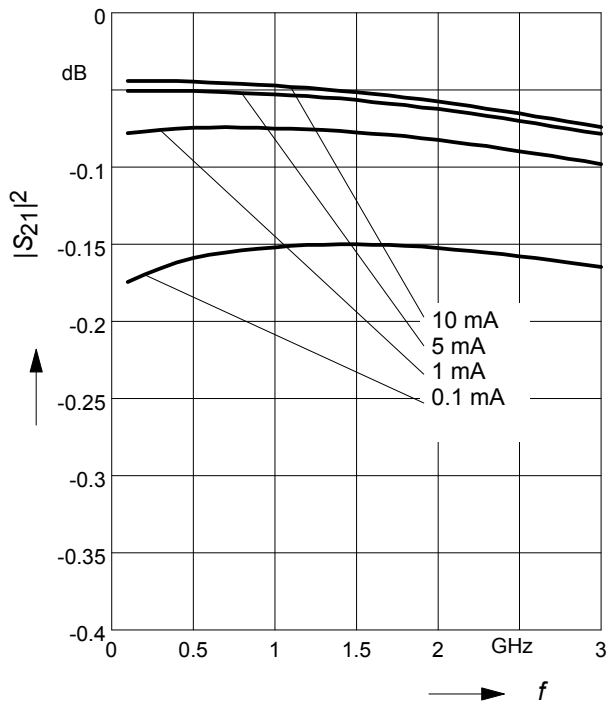
$$I_{Fmax}/I_{FDC} = f(t_p)$$

BAR65-03W

Permissible Puls Load $R_{thJS} = f(t_p)$
BAR65-07

Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

BAR65-07


Insertion loss $|S_{21}|^2 = f(f)$
 I_F = Parameter

 BAR65-02L in series configuration, $Z = 50\Omega$

Isolation $|S_{21}|^2 = f(f)$
 V_R = Parameter

 BAR65-02L in series configuration $Z = 50\Omega$
